

FJI5603D

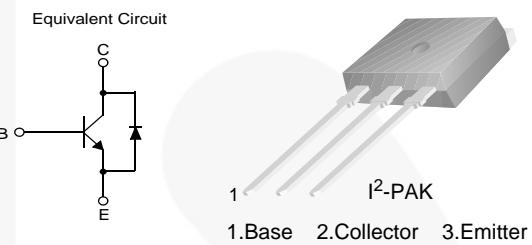
NPN Silicon Transistor

Applications

- High Voltage and High Speed Power Switch Application
- Electronic Ballast Application

Features

- Wide Safe Operating Area
- Small Variance in Storage Time
- Built-in Free Wheeling Diode



Ordering Information

Part Number	Marking	Package	Packing Method
FJI5603DTU	J5603D	TO-262 3L (I2PAK)	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	1600	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	3	A
I_{CP}	Collector Current (Pulse) ⁽¹⁾	6	A
I_B	Base Current (DC)	2	A
I_{BP}	Base Current (Pulse) ⁽¹⁾	4	A
P_C	Power Dissipation ($T_C = 25^\circ\text{C}$)	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Junction Temperature Range	-65 to +150	$^\circ\text{C}$
EAS	Avalanche Energy ($T_J = 25^\circ\text{C}$, 8 mH)	3.5	mJ

Notes:

1. Pulse test: pulse width = 5 ms, duty cycle $\leq 10\%$

Thermal Characteristics⁽²⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.25	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	80	$^\circ\text{C}/\text{W}$

Note:

2. Device mounted on minimum pad size.

Electrical Characteristics⁽³⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 0.5 \text{ mA}, I_E = 0$	1600	1689		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5 \text{ mA}, I_B = 0$	800	870		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.5 \text{ mA}, I_C = 0$	12.0	14.8		V
I_{CES}	Collector Cut-Off Current	$V_{CE} = 1600 \text{ V}, V_{BE} = 0$	$T_C = 25^\circ\text{C}$	0.01	100	μA
			$T_C = 125^\circ\text{C}$		1000	
I_{CEO}	Collector Cut-Off Current	$V_{CE} = 800 \text{ V}, I_B = 0$	$T_C = 25^\circ\text{C}$	0.01	100	μA
			$T_C = 125^\circ\text{C}$		1000	
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 12 \text{ V}, I_C = 0$		0.05	500	μA
h_{FE}	DC Current Gain	$V_{CE} = 3 \text{ V}, I_C = 0.4 \text{ A}$	$T_C = 25^\circ\text{C}$	20	29	35
			$T_C = 125^\circ\text{C}$	6	15	
		$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	$T_C = 25^\circ\text{C}$	20	43	
			$T_C = 125^\circ\text{C}$	20	46	
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 250 \text{ mA}, I_B = 25 \text{ mA}$		0.50	1.25	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.50	2.50	
		$I_C = 1 \text{ A}, I_B = 0.2 \text{ A}$		1.20	2.50	
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$T_C = 25^\circ\text{C}$	0.74	1.20	V
			$T_C = 125^\circ\text{C}$	0.61	1.10	
		$I_C = 2 \text{ A}, I_B = 0.4 \text{ A}$	$T_C = 25^\circ\text{C}$	0.85	1.20	
			$T_C = 125^\circ\text{C}$	0.74	1.10	
C_{ib}	Input Capacitance	$V_{EB} = 10 \text{ V}, I_C = 0, f = 1 \text{ MHz}$		745	1000	pF
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		56	500	pF
f_T	Current Gain Bandwidth Product	$I_C = 0.1 \text{ A}, V_{CE} = 10 \text{ V}$		5		MHz
V_F	Diode Forward Voltage	$I_F = 0.4 \text{ A}$		0.76	1.20	V
		$I_F = 1 \text{ A}$		0.83	1.50	

Note:

3. Pulse test: pulse width = 20 μs , duty cycle $\leq 10\%$.

Electrical Characteristics (Continued)

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
RESISTIVE LOAD SWITCHING (D.C. $\leq 10\%$, Pulse Width = 20 μs)						
t_{ON}	Turn-On Time	$I_C = 0.3 \text{ A}$, $I_{B1} = 50 \text{ mA}$, $I_{B2} = 150 \text{ A}$, $V_{CC} = 125 \text{ V}$, $R_L = 416 \Omega$		400	600	ns
t_{STG}	Storage Time		1.9	2.1	2.3	μs
t_F	Fall Time			310	1000	ns
t_{ON}	Turn-On Time	$I_C = 0.5 \text{ A}$, $I_{B1} = 50 \text{ mA}$, $I_{B2} = 250 \text{ mA}$, $V_{CC} = 125 \text{ V}$, $R_L = 250 \Omega$		600	1100	ns
t_{STG}	Storage Time			1.3	1.5	μs
t_F	Fall Time			180	350	ns
INDUCTIVE LOAD SWITCHING ($V_{CC} = 15 \text{ V}$)						
t_{STG}	Storage Time	$I_C = 0.3 \text{ A}$, $I_{B1} = 50 \text{ mA}$, $I_{B2} = 150 \text{ mA}$, $V_Z = 300 \text{ V}$, $L_C = 200 \text{ H}$	0.8		1.2	μs
t_F	Fall Time			170	250	ns
t_C	Cross-Over Time			180	250	ns
t_{STG}	Storage Time	$I_C = 0.5 \text{ A}$, $I_{B1} = 50 \text{ mA}$, $I_{B2} = 250 \text{ mA}$, $V_Z = 300 \text{ V}$, $L_C = 200 \text{ H}$	0.8		1.2	μs
t_F	Fall Time			140	175	ns
t_C	Cross-Over Time			170	200	ns

Typical Performance Characteristics

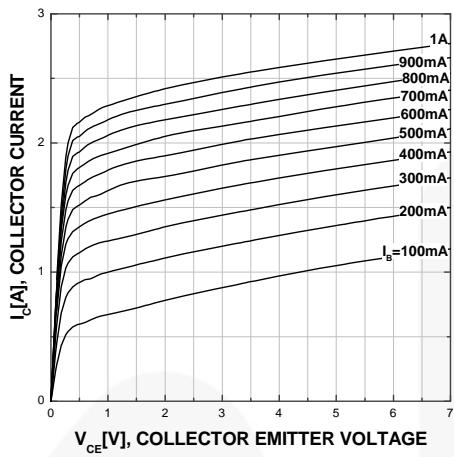


Figure 1. Static Characteristic

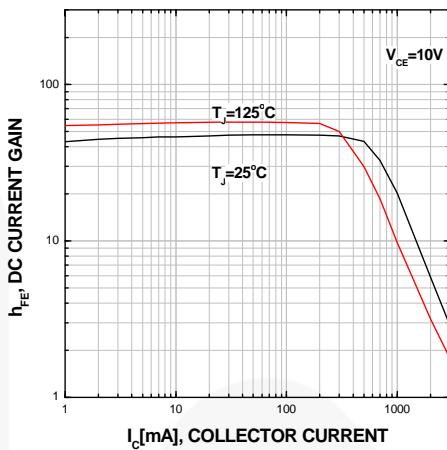


Figure 2. DC Current Gain

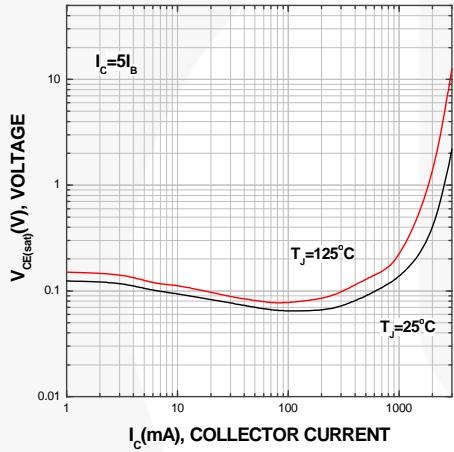


Figure 3. Collector-Emitter Saturation Voltage

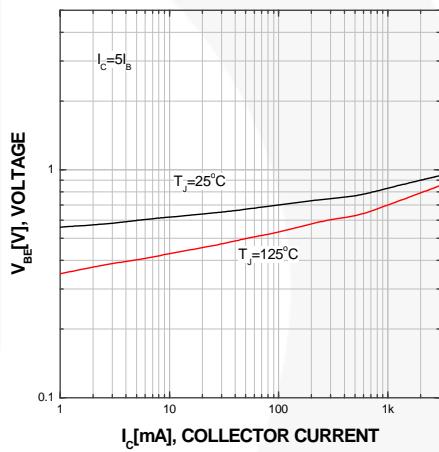


Figure 4. Base-Emitter Saturation Voltage

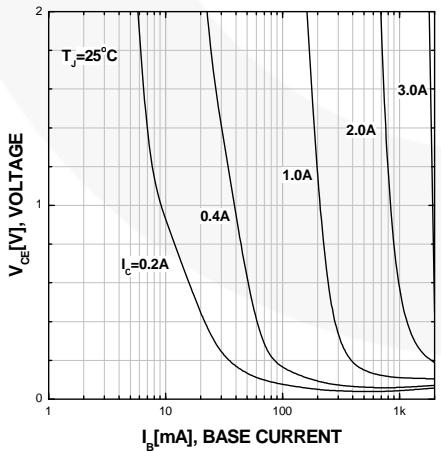


Figure 5. Typical Collector Saturation Voltage

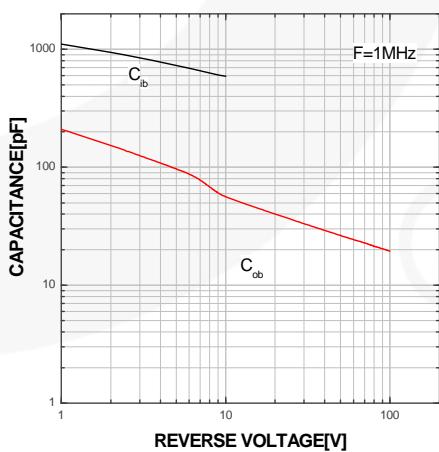


Figure 6. Capacitance

Typical Performance Characteristics (Continued)

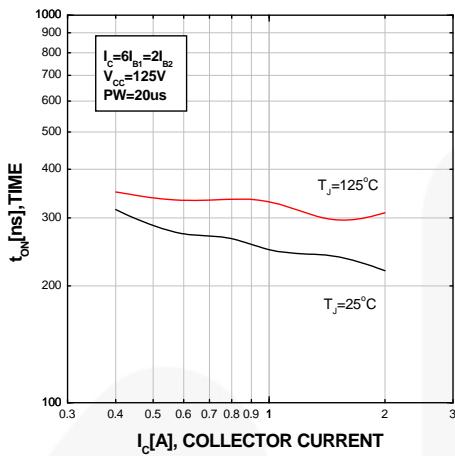


Figure 7. Resistive Switching Time, t_{on}

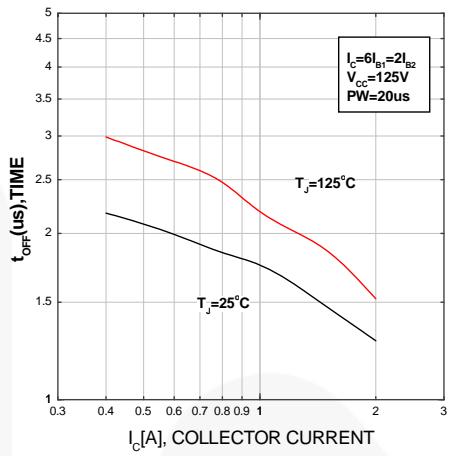


Figure 8. Resistive Switching Time, t_{off}

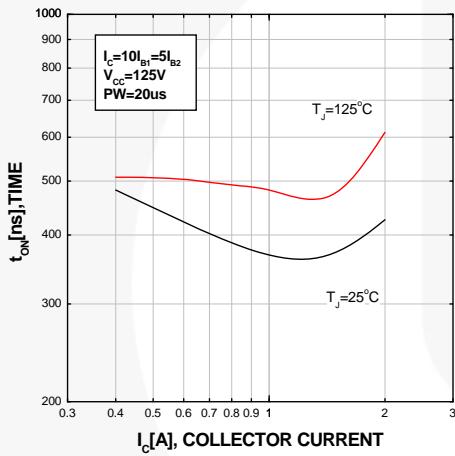


Figure 9. Resistive Switching Time, t_{on}

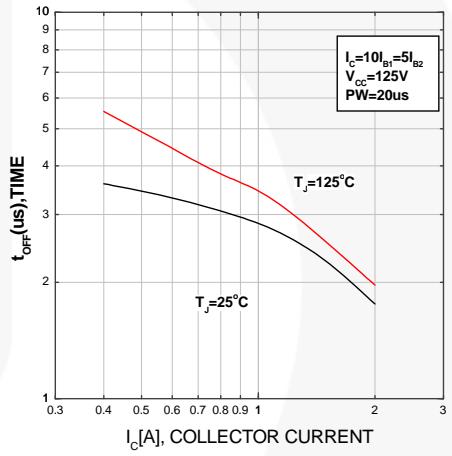


Figure 10. Resistive Switching Time, t_{off}

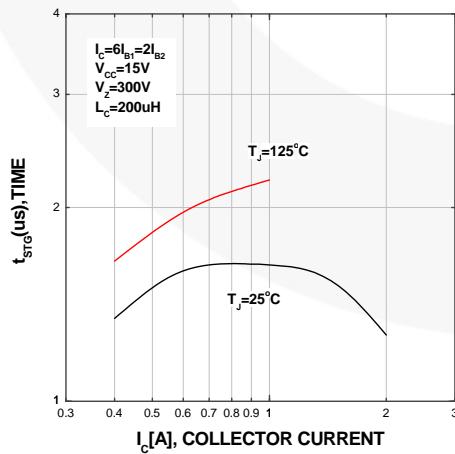


Figure 11. Inductive Switching Time, t_{STG}

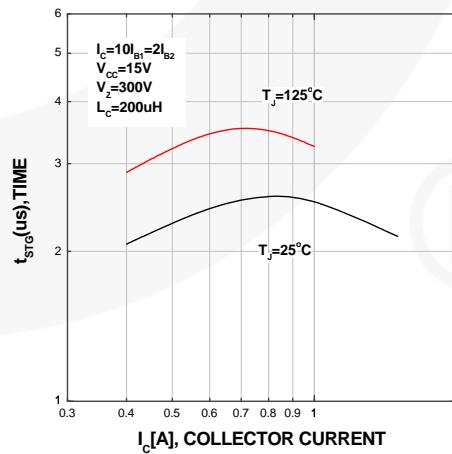


Figure 12. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

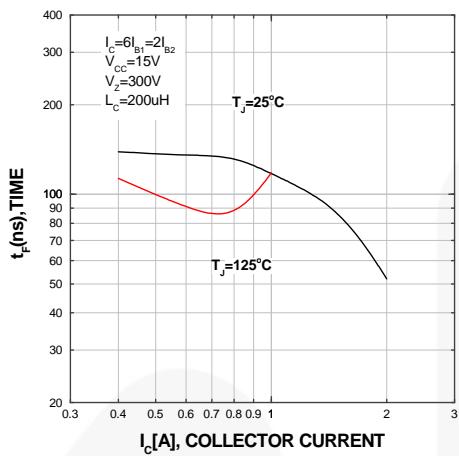


Figure 13. Inductive Switching Time, t_f

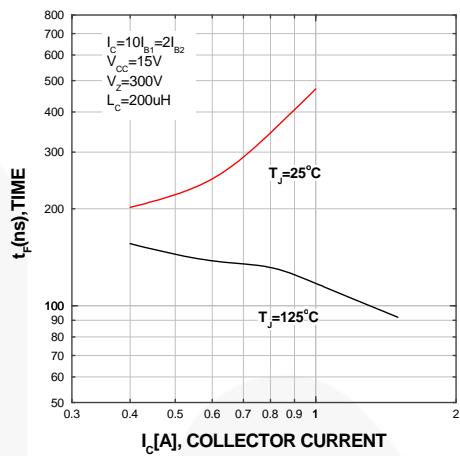


Figure 14. Inductive Switching Time, t_f

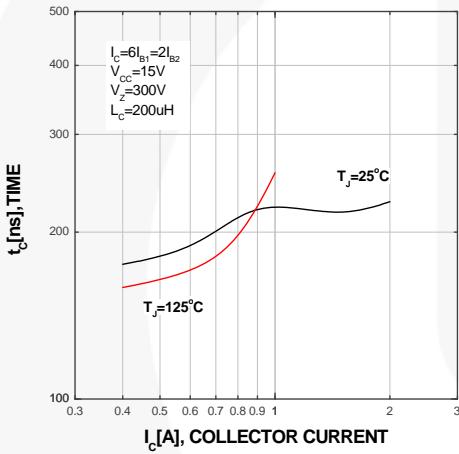


Figure 15. Inductive Switching Time, t_c

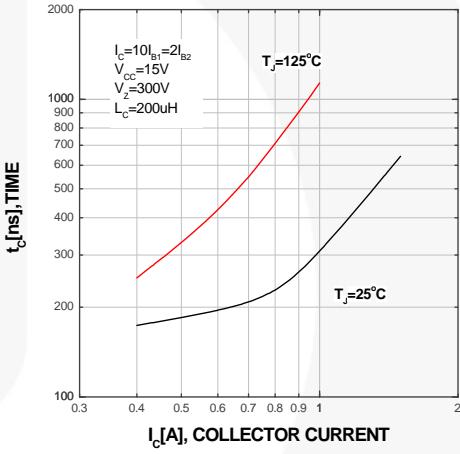


Figure 16. Inductive Switching Time, t_c

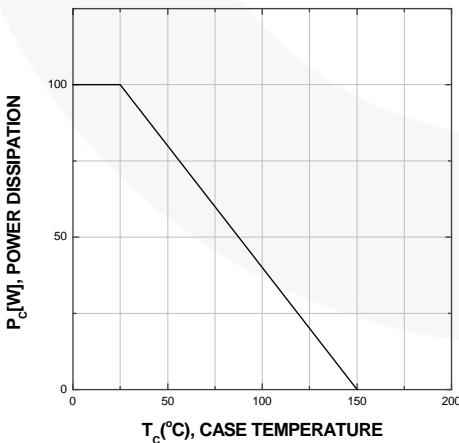
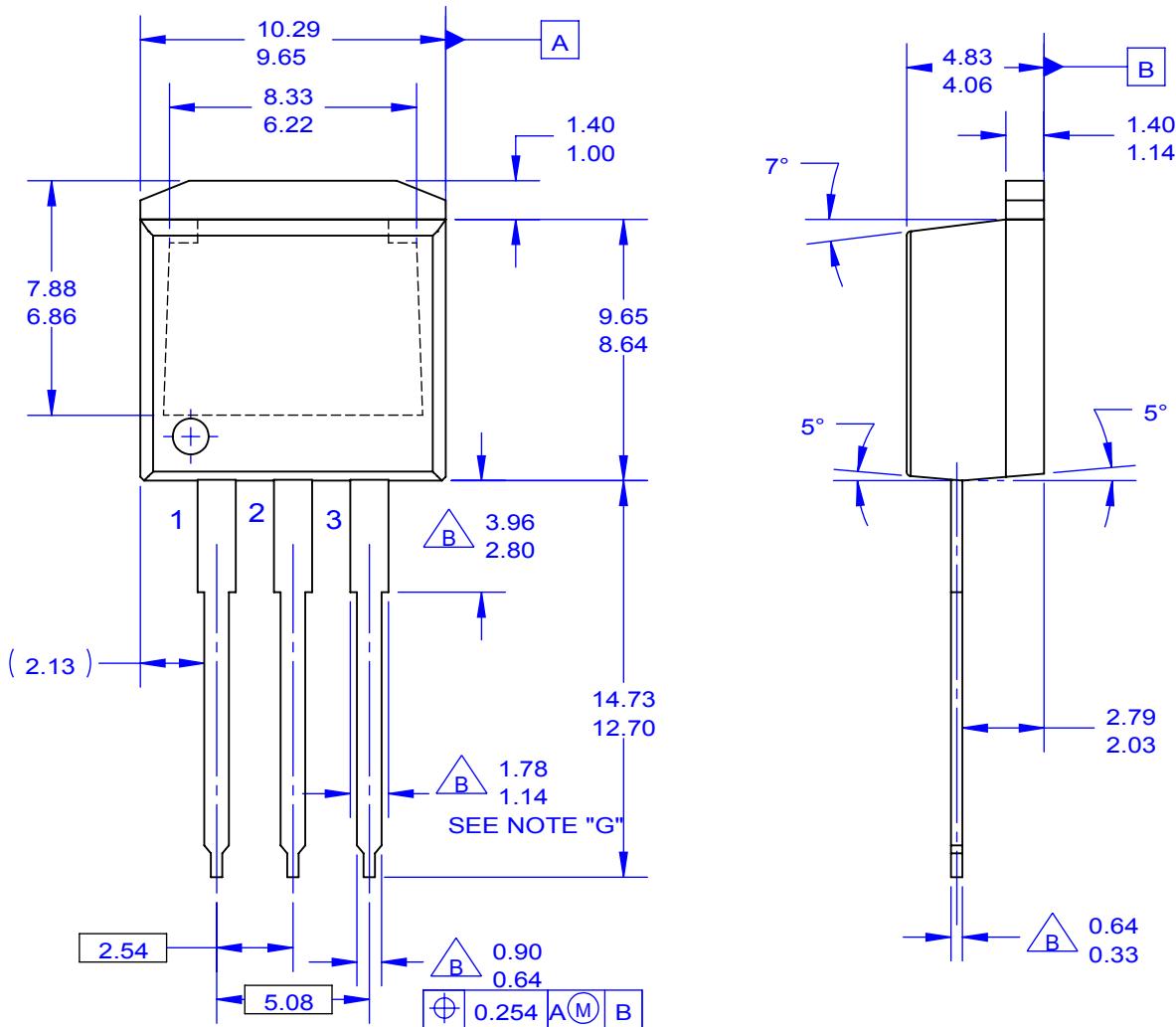


Figure 17. Power Derating



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO
TO262 JEDEC VARIATION AA.
-  B. DOES NOT COMPLY JEDEC STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ANSI
Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY
(LOWER LEFT CORNER, LOWER CENTER
AND CENTER OF PACKAGE)
- G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
- H. DRAWING FILE NAME: TO262A03REV6



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Definition of Terms

Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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